AMENDMENTS TO THE CLAIMS

Please amend Claims as follows. Insertions are shown underlined while deletions are ~~struck through~~.

1 (currently amended): A polishing pad used for chemical mechanical polishing comprising:

a polishing region; and

a light-transmitting region constituted by a material having a ΔT of 10 ~~(%)~~ or less which is defined by the equation

$$\Delta T = T_0 - T_1$$

wherein ~~ΔT (%) is a difference between T_0 (%) and T_1 (%) as measured over the whole range of measurement wavelengths of from 400 to 700 nm, wherein~~ T_1 is a light transmittance ~~(%)~~ of the material ~~of~~ for the light-transmitting region in percentage as measured at ~~the measurement~~ a plurality of wavelengths between 400 and 700 nm ~~λ~~ after dipping the material in a KOH aqueous solution at pH 11 for 24 hours and T_0 is a light-transmittance ~~(%)~~ of the material in percentage as measured at the plurality of ~~measurement~~ wavelengths ~~λ~~ before the dipping,

wherein ~~the material of~~ the light-transmitting region ~~is formed~~ comprises a polyurethane resin comprising 4,4'-diphenylmethane diisocyanate as an organic isocyanate and at least one high-molecular-weight poltol selected from the group consisting of ~~from (i)~~ polycaprolactone polyol, ~~(ii)~~ polyester polycarbonate polyol, ~~or (iii)~~and polyester polyol formed from adipic acid, hexane diol, and ethylene glycol,

whereby the change rate in the light transmittance of the light-transmitting region in measurement wavelengths of 400 to 700 nm before dipping is 50 (%) or less,

wherein the change rate (%) = {(maximum light transmittance in 400 to 700 nm – minimum light transmittance in 400 to 700 nm)/maximum light transmittance in 400 to 700 nm}×100.

2 (currently amended): A polishing pad used for chemical mechanical polishing comprising:

a polishing region; and

a light-transmitting region constituted by a material having a ΔT of 10 ~~(%)~~ or less which is defined by the equation

$\Delta T = T_0 - T_1$

wherein ~~ΔT (%) is a difference between T_0 (%) and T_1 (%) as measuredover the whole range of measurement wavelengths of from 400 to 700 nm, wherein~~ T_1 is a light transmittance ~~(%)~~ of the material ~~of~~ for the light-transmitting region in percentage as measured at ~~the measurement~~ a plurality of wavelengths between 400 and 700 nm~~λ~~ after dipping the material in an H_2O_2 aqueous solution at pH 11 for 24 hours and T_0 is a light-transmittance ~~(%)~~ of the material in percentage as measured at the plurality of ~~measurement~~ wavelengths ~~λ~~ before the dipping,

wherein ~~the material of~~ the light-transmitting region ~~is formed~~ comprises a polyurethane resin comprising 4,4'-diphenylmethane diisocyanate as an organic isocyanate and at least one high-molecular-weight poltol selected from the group consisting of ~~from (i)~~ polycaprolactone polyol, ~~(ii)~~ polyester polycarbonate polyol, ~~or (iii)~~and polyester polyol formed from adipic acid, hexane diol, and ethylene glycol,

whereby the change rate in the light transmittance of the light-transmitting region in measurement wavelengths of 400 to 700 nm before dipping is 50 (%) or less,

wherein the change rate (%) = {(maximum light transmittance in 400 to 700 nm – minimum light transmittance in 400 to 700 nm)/maximum light transmittance in 400 to 700 nm}×100.

3 (previously presented): The polishing pad according to claim 1, wherein the material forming the light transmitting region is non-form.

4 (previously presented): The polishing pad according to claim 1, wherein the material forming the polishing region is fine-cell foam.

5 (canceled):

6 (previously presented): The polishing pad according to claim 1, wherein the polishing region at the polishing side is provided with grooves.

7 (currently amended): A method of manufacturing a semiconductor device, which comprises:

(i) providing a polishing pad comprising:

a polishing region; and

a light-transmitting region constituted by a material having a ΔT of 10 ~~(%)~~ or less which is defined by the equation

$\Delta T = T_0 - T_1$

wherein ~~ΔT (%) is a difference between T_0 (%) and T_1 (%) as measured over the whole range of measurement wavelengths of from 400 to 700 nm, wherein~~ T_1 is a light transmittance ~~(%)~~ of the material ~~of~~for the light-transmitting region in percentage as measured at ~~the measurement~~a plurality of wavelength between 400 and 700nm ~~λ~~ after dipping the material in a KOH aqueous solution at pH 11 for 24 hours and T_0 is a light-transmittance ~~(%)~~ of the material in percentage as measured at the plurality of the ~~measurement~~ wavelengths ~~λ~~ before the dipping,

wherein ~~the material of~~ the light-transmitting region ~~is formed~~ comprises a polyurethane resin comprising 4,4'-diphenylmethane diisocyanate as an organic isocyanate and at least one high-molecular-weight poltol selected from the group consisting of ~~from (i)~~ polycaprolactone polyol, ~~(ii)~~ polyester polycarbonate polyol, ~~or (iii)~~and polyester polyol formed from adipic acid, hexane diol, and ethylene glycol,

whereby the change rate in the light transmittance of the light-transmitting region in measurement wavelengths of 400 to 700 nm before dipping is 50 (%) or less,

wherein the change rate (%) = {(maximum light transmittance in 400 to 700 nm – minimum light transmittance in 400 to 700 nm)/maximum light transmittance in 400 to 700 nm}×100; and

(ii) polishing the surface of a semiconductor wafer with the polishing pad .

8 (canceled):

9 (previously presented): The polishing pad according to 2, wherein the material forming the polishing region is fine-cell foam.

10 (previously presented): The polishing pad according to 3, wherein the material forming the polishing region is fine-cell foam.

11-13 (canceled):

14 (previously presented): The polishing pad according to claim 2, wherein the polishing region at the polishing side is provided with grooves.

15 (previously presented): The polishing pad according to claim 3, wherein the polishing region at the polishing side is provided with grooves.

16 (previously presented): The polishing pad according to claim 4, wherein the polishing region at the polishing side is provided with grooves.

17 (canceled):

18 (currently amended): A method of manufacturing a semiconductor device, which comprises:

(i) providing a polishing pad comprising:

a polishing region; and

a light-transmitting region constituted by a material having a ΔT of 10 ~~(%)~~ or less which is defined by the equation

$$\Delta T = T_0 - T_1$$

wherein ~~ΔT (%) is a difference between T_0 (%) and T_1 (%) as measured over the whole range of measurement wavelengths of from 400 to 700 nm, wherein~~ T_1 is a light transmittance ~~(%)~~ of the material ~~of~~for the light-transmitting region in percentage as measured at ~~the measurement~~ a plurality of wavelengths ~~λ~~ between 400 and 700 nm after dipping the material in an H_2O_2 aqueous solution at pH 11 for 24 hours and T_0 is a light-transmittance (%) of the material in percentage as measured at the plurality of the ~~measurement~~ wavelengths ~~λ~~ before the dipping,

wherein ~~the material of~~ the light-transmitting region ~~is formed~~ comprises a polyurethane resin comprising 4,4'-diphenylmethane diisocyanate as an organic isocyanate and at least one high-molecular-weight poltol selected from the group consisting of ~~from (i)~~ polycaprolactone polyol, ~~(ii)~~ polyester polycarbonate polyol, ~~or (iii)~~and polyester polyol formed from adipic acid, hexane diol, and ethylene glycol,

whereby the change rate in the light transmittance of the light-transmitting region in measurement wavelengths of 400 to 700 nm before dipping is 50 (%) or less,

wherein the change rate (%) = {(maximum light transmittance in 400 to 700 nm – minimum light transmittance in 400 to 700 nm)/maximum light transmittance in 400 to 700 nm}×100; and

(ii) polishing the surface of a semiconductor wafer with the polishing pad.

19 (currently amended): A polishing pad for chemical mechanical polishing comprising:

a polishing region having a through-hole in an axial direction; and

a light-transmitting region fitted in the through-hole, said light-transmitting region being constituted by a material having a ΔT of 10 ~~(%)~~ or less which is defined by the equation

$$\Delta T = T_0 - T_1$$

wherein ~~ΔT is a difference between T_0 (%) and T_1 (%) as measured over the whole range of measurement wavelengths of from 400 to 700 nm, wherein~~ T_1 is a light transmittance ~~(%)~~ of the material ~~of~~for the light-transmitting region in percentage as measured at a plurality of ~~measurement~~ wavelengths between 400 to 700nm~~λ~~ after dipping the material for 24 hours in a KOH aqueous solution having a pH of 11 or in an H_2O_2 aqueous solution having pH of 4, and T_0 is a light-transmittance ~~(%)~~ of the material in percentage as measured at the plurality of ~~measurement~~the -wavelengths ~~λ~~ before the dipping,

wherein ~~the material of~~ the light-transmitting region ~~is formed~~ comprises a polyurethane resin comprising 4,4'-diphenylmethane diisocyanate as an organic isocyanate and at least one high-molecular-weight poltol selected from the group consisting of ~~from (i)~~ polycaprolactone polyol, ~~(ii)~~ polyester polycarbonate polyol, ~~or (iii)~~and polyester polyol formed from adipic acid, hexane diol, and ethylene glycol,

whereby the change rate in the light transmittance of the light-transmitting region in measurement wavelengths of 400 to 700 nm before dipping is 50 (%) or less,

wherein the change rate (%) = {(maximum light transmittance in 400 to 700 nm – minimum light transmittance in 400 to 700 nm)/maximum light transmittance in 400 to 700 nm}×100.

20 (canceled):

21 (previously presented): The polishing pad according to claim 19, further comprising a cushion layer laminated on a back side of the polishing region opposite to its polishing side, wherein the cushion layer has a through-hole at the same position as the light-transmitting region with respect to the axial direction.

22 (previously presented): The polishing pad according to claim 21, wherein the cushion layer is laminated on the polishing region using a double-coated tape.

23 (previously presented): The polishing pad according to claim 19, wherein the material is a polyurethane resin comprising an organic isocyanate, a polyol, and a chain extender.

24 (previously presented): The polishing pad according to claim 23, wherein in the polyurethane resin, a ratio of the number of isocyanate groups of the organic isocyanate to the number of functional groups of the polyol and the chain extender in total is 0.95 to 1.15.